



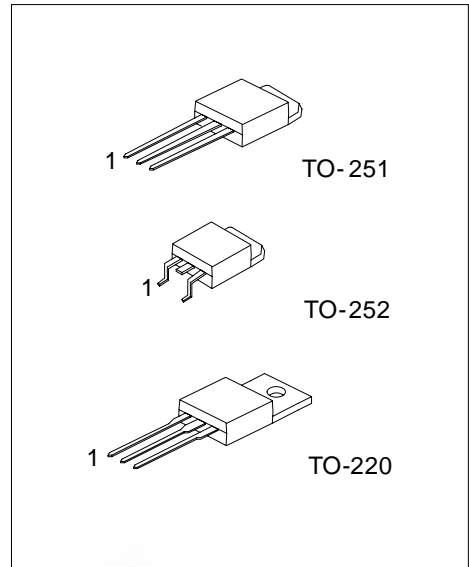
## MJE3055T

### NPN SILICON TRANSISTOR

## HIGH VOLTAGE TRANSISTOR

### DESCRIPTION

The UTC **MJE3055T** is designed for general purpose of amplifier and switching applications.



\*Pb-free plating product number: MJE3055TL

### ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
MJE3055T-TA3-T	MJE3055TL-TA3-T	TO-220	B	C	E	Tube
MJE3055T-TM3-T	MJE3055TL-TM3-T	TO-251	B	C	E	Tube
MJE3055T-TN3-R	MJE3055TL-TN3-R	TO-252	B	C	E	Tape Reel
MJE3055T-TN3-T	MJE3055TL-TN3-T	TO-252	B	C	E	Tube

<p>MJE3055TL-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Lead Plating</p>	<p>(1) R: Tape Reel, T: Tube</p> <p>(2) TA3: TO-220, TM3: TO-251, TN3: TO-252</p> <p>(3) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (T<sub>c</sub>=25 )

(Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	70	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Total Power Dissipation	TO-220	75	W
	TO-251/TO-252	20	W
Collector Current	I <sub>C</sub>	10	A
Base Current	I <sub>B</sub>	6	A
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25 , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =200mA	60			V
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =10mA	70			V
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =10mA	5			V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =70V			1	mA
	I <sub>CEO</sub>	V <sub>CE</sub> =30V			700	μA
	I <sub>CEX</sub>	V <sub>CE</sub> =70V, V <sub>EB(OFF)</sub> =1.5V			1	mA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V			5	mA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)1</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.4A			1.1	V
	V <sub>CE(SAT)2</sub>	I <sub>C</sub> =10A, I <sub>B</sub> =3.3A			8	V
Base-Emitter on Voltage	V <sub>BE(ON)</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =4A			1.8	V
DC Current Gain	h <sub>FE1</sub>	I <sub>C</sub> =4A, V <sub>CE</sub> =4V	20		100	
	h <sub>FE2</sub>	I <sub>C</sub> =4A, V <sub>CE</sub> =10V	5			
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=1MHz	2			MHZ

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